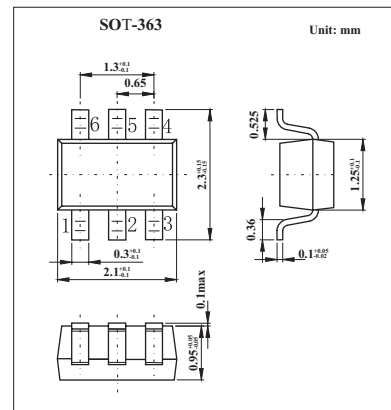


Dual Schottky Barrier Diodes

MBD110DWT1
MBD330DWT1;MBD770DWT1
■ Features

- Extremely Low Minority Carrier Lifetime
- Very Low Capacitance
- Low Reverse Leakage


■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	MBD110DWT1 7	Vdc
		MBD330DWT1 30	
		MBD770DWT1 70	
Forward Power Dissipation TA = 25 °C	P _F	120	mA
Junction Temperature	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

MBD110DWT1 MBD330DWT1;MBD770DWT1

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	MBD110DWT1	$I_R = 10 \mu A$	7.0	10		Volts
	MBD330DWT1		30			
	MBD770DWT1		70			
Diode Capacitance	MBD110DWT1	$V_R = 0, f = 1.0 \text{ MHz}$		0.88	1.0	pF
Total Capacitance	MBD330DWT1	$V_R = 15 \text{ Volts}, f = 1.0 \text{ MHz}$		0.9	1.5	pF
	MBD770DWT1	$V_R = 20 \text{ Volts}, f = 1.0 \text{ MHz}$		0.5	1.0	
Reverse Leakage	MBD110DWT1	$V_R = 3.0 \text{ V}$		0.02	0.25	μA
	MBD330DWT1	$V_R = 25 \text{ V}$		13	200	nAdc
	MBD770DWT1	$V_R = 35 \text{ V}$		9	200	nAdc
Noise Figure	MBD110DWT1	$f = 1.0 \text{ GHz}$		6		dB
Forward Voltage	MBD110DWT1	$I_F = 10 \text{ mA}$		0.5	0.6	Vdc
	MBD330DWT1	$I_F = 1.0 \text{ mAdc}$		0.38	0.45	
	MBD770DWT1	$I_F = 10 \text{ mA}$		0.52	0.6	
		$I_F = 1.0 \text{ mAdc}$		0.47	0.5	
		$I_F = 10 \text{ mA}$		0.7	1.0	

■ Marking

Type	MBD110DWT1	MMBD330DWT1	MBD770DWT1
Marking	M4	T4	H5